

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE2010E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

General Features

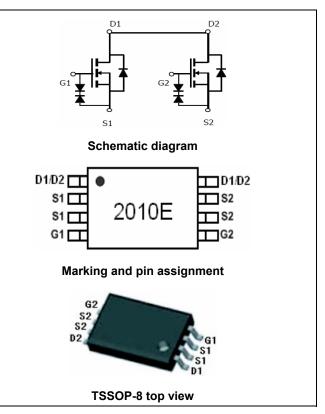
• V_{DS} = 20V,I_D =7A

$$\begin{split} & R_{DS(ON)} < 24m\Omega @ V_{GS} = 2.5V \\ & R_{DS(ON)} < 18m\Omega @ V_{GS} = 4.5V \\ & \text{ESD Rating: } 2000V \text{ HBM} \end{split}$$

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- ●PWM application
- Load switch



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2010E	NCE2010E	TSSOP-8	Ø330mm	12mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	20	V	
Gate-Source Voltage	Vgs	±12	V	
Drain Current-Continuous	I _D	7	A	
Drain Current-Pulsed (Note 1)	I _{DM}	30	A	
Maximum Power Dissipation	PD	1.5	W	
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 150	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	83.3	°C/W
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Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	21.5	23	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =20V, V_{GS} =0V	-	-	1	μA



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Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.7	0.9	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =6.5A	-	13	18	mΩ
Drain-Source On-State Resistance		V _{GS} =2.5V, I _D =5.5A	-	17	24	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =7A	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	1150	-	PF
Output Capacitance	Coss	V_{DS} =10V, V_{GS} =0V,	-	185	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	145	-	PF
Switching Characteristics (Note 4)				•		
Turn-on Delay Time	t _{d(on)}		-	6		nS
Turn-on Rise Time	tr	V_{DD} =10V,R _L =1.35 Ω	-	13		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =5V, R_{GEN} =3 Ω	-	52		nS
Turn-Off Fall Time	t _f		-	16		nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =7A, V _{GS} =4.5V	-	15		nC
Gate-Source Charge	Q _{gs}		-	0.8	-	nC
Gate-Drain Charge	Q _{gd}	v _{GS} =4.5v	-	3.2	-	nC
Drain-Source Diode Characteristics			•	•		•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	7	А

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



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Typical Electrical and Thermal Characteristics

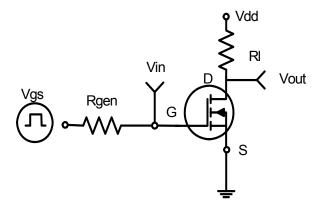
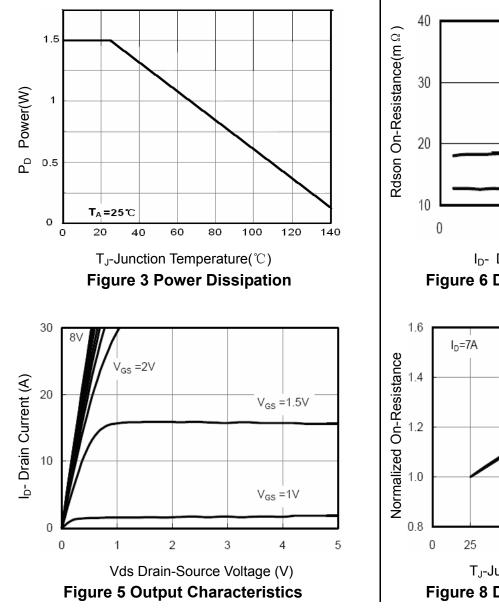


Figure 1:Switching Test Circuit



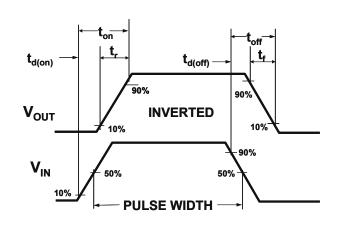
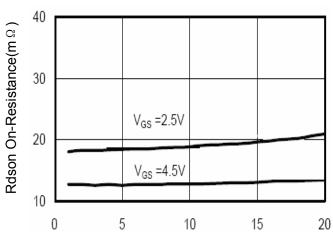
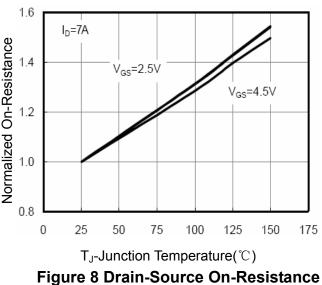


Figure 2:Switching Waveforms



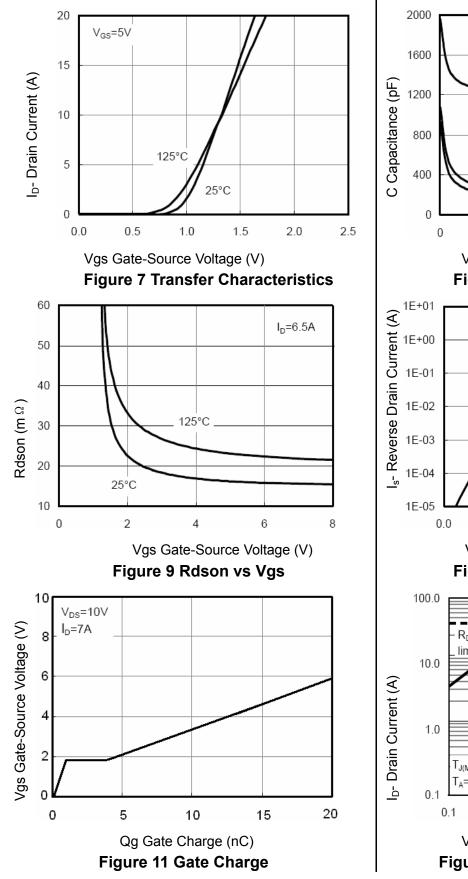
I_D- Drain Current (A) Figure 6 Drain-Source On-Resistance

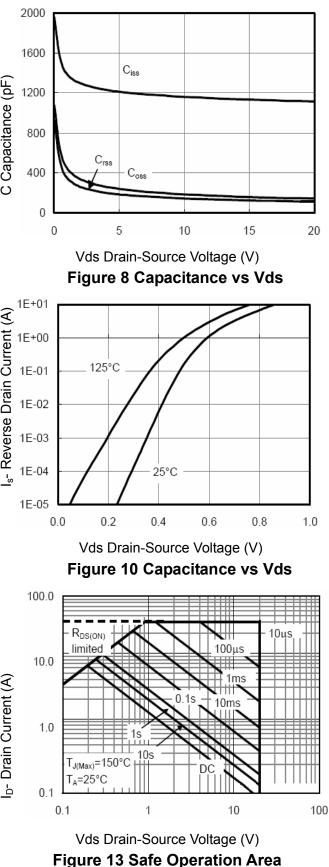




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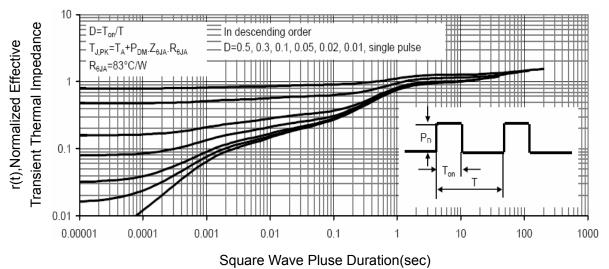


Figure 14 Normalized Maximum Transient Thermal Impedance

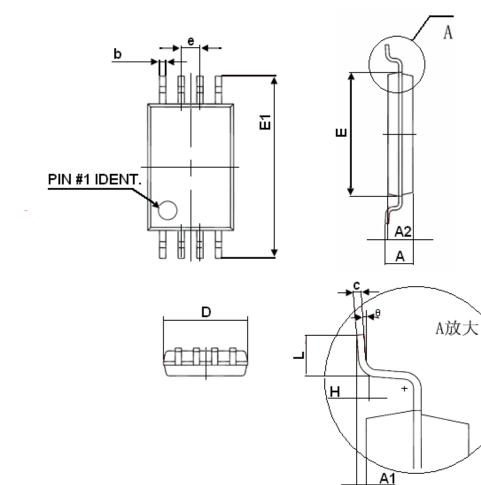
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Tssop-8 Package Information



Symbol	Dimensions In Millimeters			
Symbol	Min	Max		
D	2.900	3.100		
E	4.300	4.500		
b	0.190	0.300		
С	0.090	0.200		
E1	6.250	6.550		
Α		1.100		
A2	0.800	1.000		
A1	0.020	0.150		
е	0.65(BSC)			
L	0.500	0.700		
Н	0.2	5(TYP)		
Θ	1° 7°			





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